

said interlayer insulating film and extending over a part of said interlayer insulating film, a capacitor insulating film formed for coverage over said storage node and said interlayer insulating film, and a plate electrode formed in opposed relation with said storage node via said capacitor insulating film,

D1
Cont. said first insulating film defining said interlayer insulating film,

said second insulating film defining said capacitor insulating film,

said supporting film is interposed between said interlayer insulating film and said capacitor insulating film.

Please add new claims 37 and 38 as follows:

D2 --37. (New) A semiconductor device as set forth in claim 1, wherein said supporting film does not reflow due to said heat treatment which causes said first insulating film to reflow.

38. (New) A semiconductor device as set forth in claim 4, where said second insulating film is formed directly on the surface of said supporting film.--

REMARKS

I. Introduction

In response to the pending Office Action, Applicants have cancelled claim 34, without prejudice, and have amended claim 4 so as to address the objection to the drawings. In addition, new claims 37 and 38 have been added to recite additional aspects of the present invention not previously claimed. No new matter has been added.